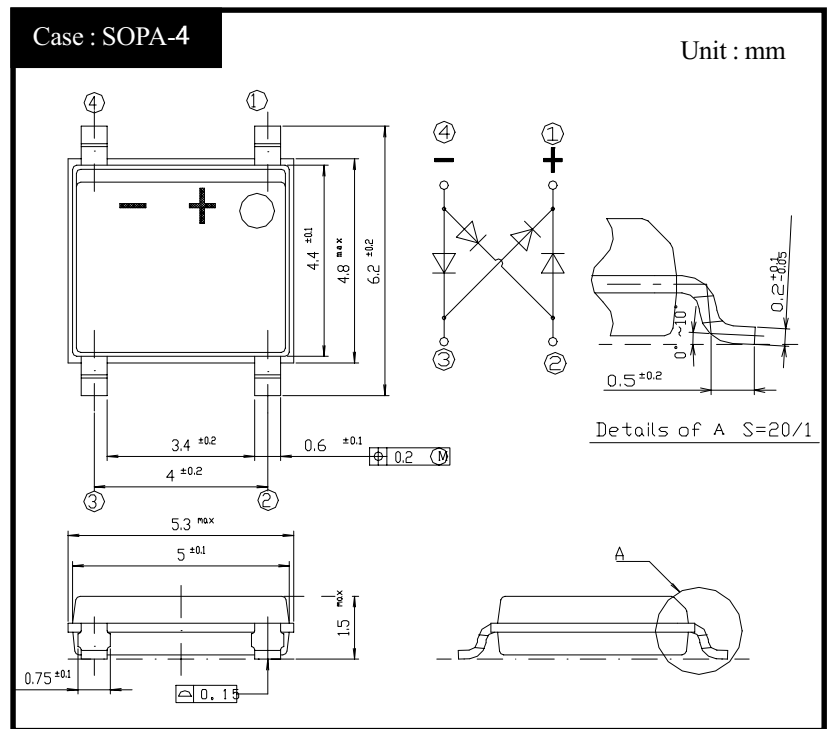


D1UBA80

800V 1A

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings (If not specified $T_I=25^\circ\text{C}$)

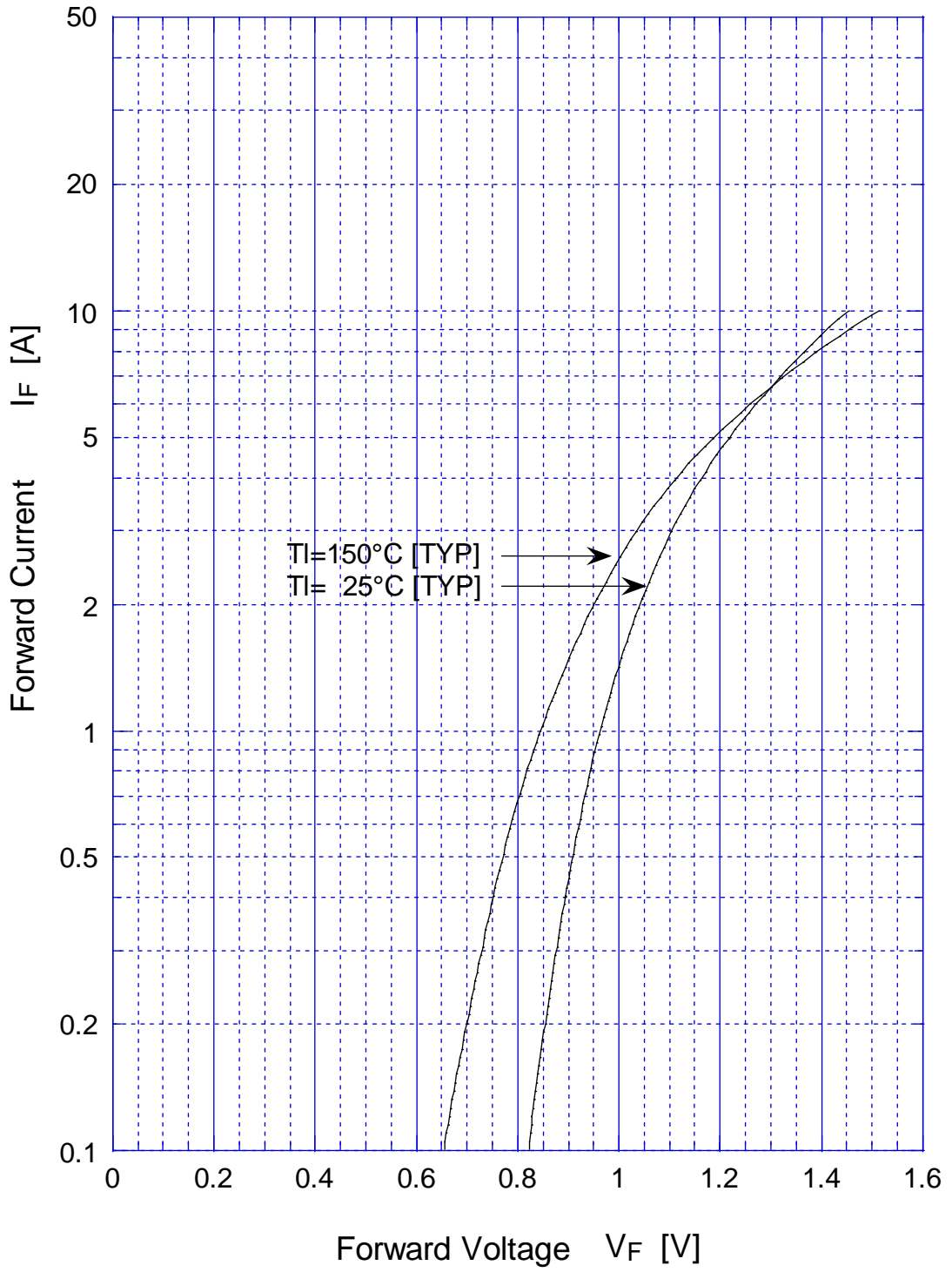
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T_{stg}		-55~150	$^\circ\text{C}$
Operating Junction Temperature	T_j		150	$^\circ\text{C}$
Maximum Reverse Voltage	V_{RM}		800	V
Average Rectified Forward Current	I_o	50Hz sine wave, R-load, On alumina substrate $T_a=25^\circ\text{C}$	1.0	A
		50Hz sine wave, R-load, On glass-epoxy substrate $T_a=25^\circ\text{C}$	0.8	
Peak Surge Forward Current	I_{FSM}	50Hz sine wave, Non-repetitive 1 cycle peak value, $T_j=25^\circ\text{C}$	30	A
Current Squared Time	I^2_t	$1\text{ms} \leq t < 10\text{ms}$ $T_j=25^\circ\text{C}$	3	A^2s

● Electrical Characteristics (If not specified $T_I=25^\circ\text{C}$)

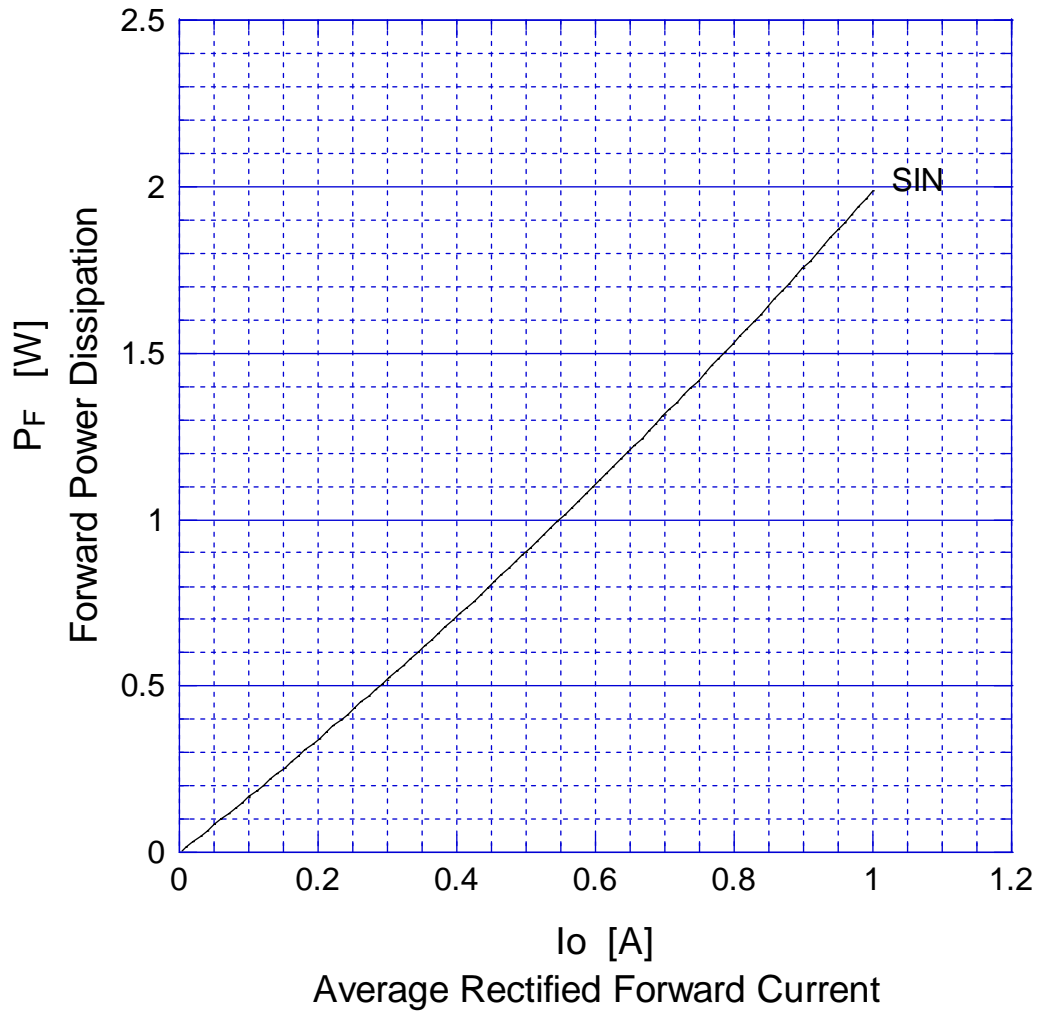
Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	V_F	$I_F=0.4\text{A}$, Pulse measurement, Rating of per diode	Max 0.95	V
Reverse Current	I_R	$V_R=800\text{V}$, Pulse measurement, Rating of per diode	Max 10	μA
Thermal Resistance	θ_{jl}	junction to lead	Max 25	$^\circ\text{C/W}$
	θ_{ja}	junction to ambient, On alumina substrate	Max 62.5	
		junction to ambient, On glass-epoxy substrate	Max 80	

D1UBA80 Forward Voltage

Pulse measurement per diode

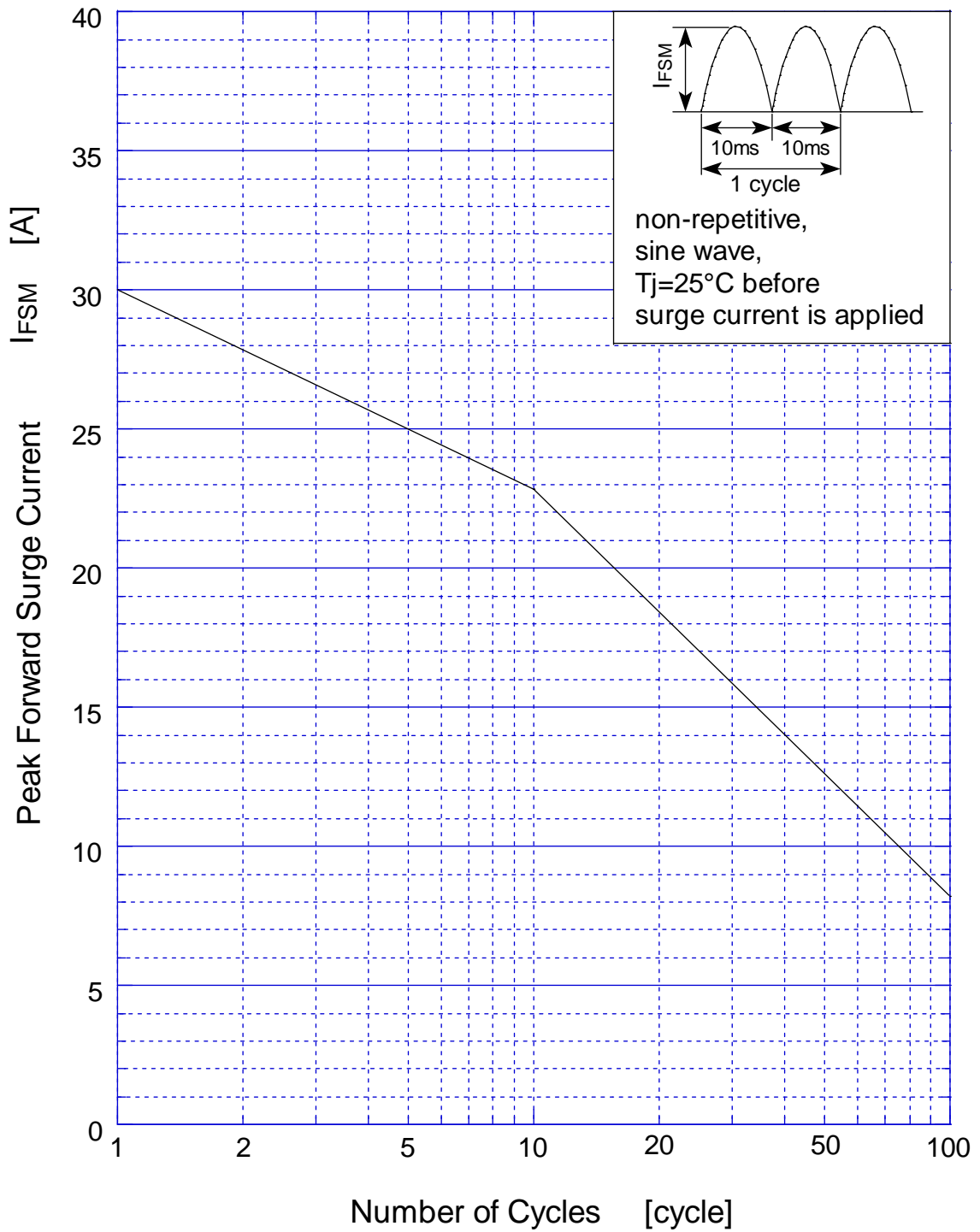


D1UBA80 Forward Power Dissipation



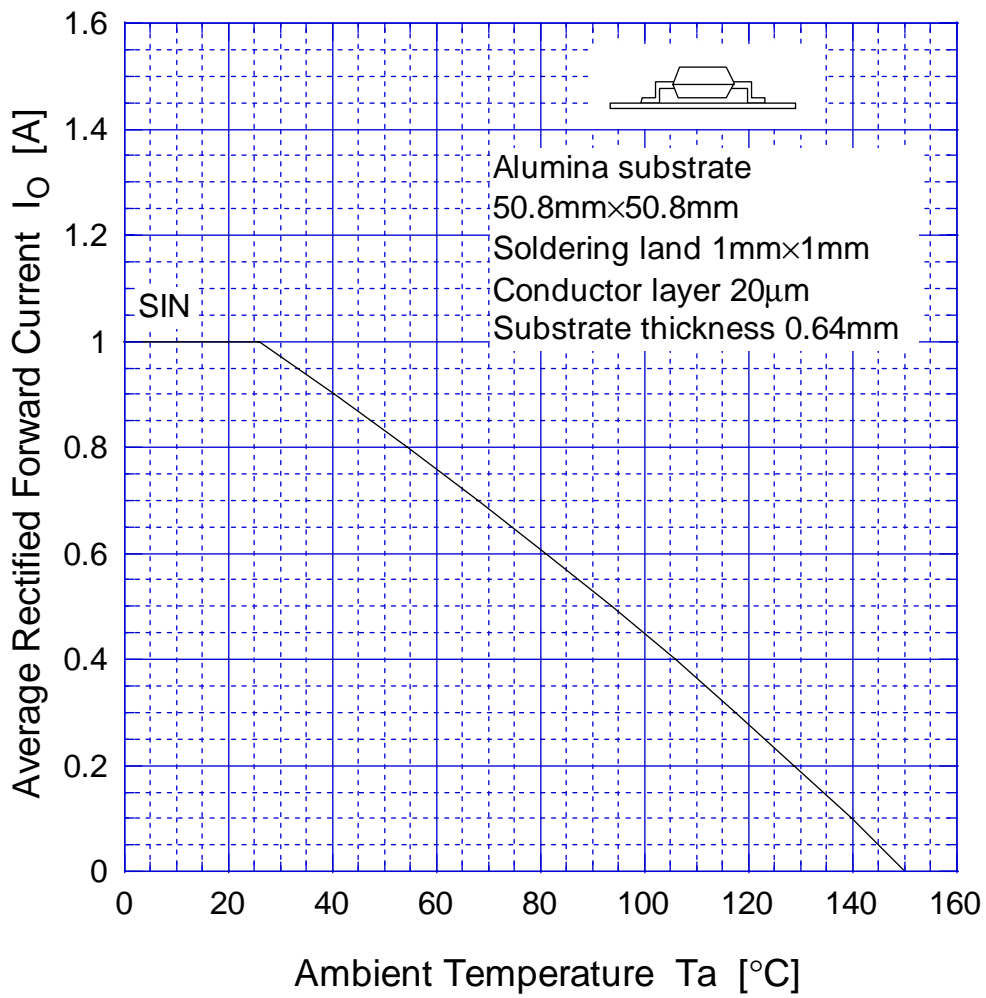
$T_j = 150^\circ\text{C}$

D1UBA80 Peak Surge Forward Capability



D1UBA80

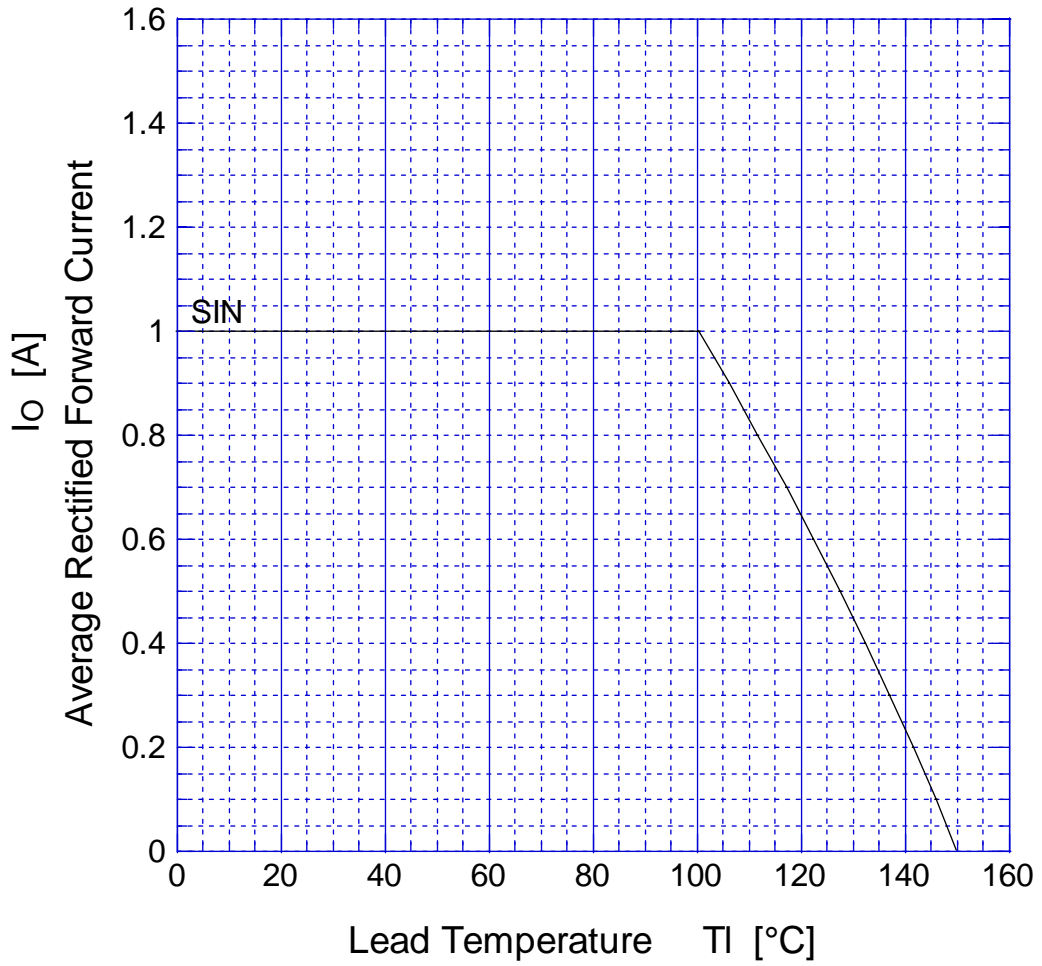
Derating Curve



$$V_R = V_{RM}$$

D1UBA80

Derating Curve



$$V_R = V_{RM}$$